

The documentation and process conversion measures necessary to comply with this revision shall be completed by 14 October 2000.

INCH-POUND

MIL-PRF-19500/394E  
 14 July 2000  
 SUPERSEDING  
 MIL-PRF-19500/394D  
 20 December 1998

PERFORMANCE SPECIFICATION

SEMICONDUCTOR DEVICE, TRANSISTOR, NPN, SILICON, POWER SWITCHING  
 TYPES: 2N4150, 2N5237, 2N5238, 2N4150S, 2N5237S, AND 2N5238S  
 JAN, JANTX, JANTXV, JANS, JANHC AND JANKC

This specification is approved for use by all Departments and Agencies of the Department of Defense.

1. SCOPE

1.1 Scope. This specification covers the performance requirements for NPN, silicon, low-power, high voltage transistors. Four levels of product assurance are provided for each encapsulated device type as specified in MIL-PRF-19500 and two levels of product assurance are provided for each unencapsulated device type.

1.2 Physical dimensions. See figures 1 (TO- 5) and 2 (JANHC and JANKC).

1.3 Maximum ratings.

Types	P <sub>T</sub> (1) T <sub>A</sub> = +25°C	P <sub>T</sub> (2) T <sub>C</sub> = +25°C	V <sub>CBO</sub>	V <sub>CEO</sub>	V <sub>EBO</sub>	I <sub>C</sub>	T <sub>STG</sub> and T <sub>OP</sub>	R <sub>θJC</sub> (max)	R <sub>θJA</sub> (min)
	<u>W</u>	<u>W</u>	<u>V dc</u>	<u>V dc</u>	<u>V dc</u>	<u>A dc</u>	<u>°C</u>	<u>°C/mW</u>	<u>°C/mW</u>
2N4150, S	1.0	5.0	100	70	10	10	-65 to +200	.020	.175
2N5237, S	1.0	5.0	150	120	10	10	-65 to +200	.020	.175
2N5238, S	1.0	5.0	200	170	10	10	-65 to +200	.020	.175

(1) Derate linearly 5.7 mW/°C for T<sub>A</sub> > +25°C.

(2) Derate linearly 50 mW/°C for T<sub>C</sub> > +25°C.

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Commander, Defense Supply Center Columbus, ATTN: DSCC-VAC, P.O. Box 3990, Columbus, OH 43216-5000, by using the Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

1.4 Primary electrical characteristics.

	$h_{FE2}$ (1)	$h_{FE3}$ (1)	$C_{obo}$	$h_{fe}$	$V_{BE(sat)}$ (1)	$V_{CE(sat)}$
Limits	$I_C = 5 \text{ A dc}$ $V_{CE} = 5 \text{ V dc}$	$I_C = 10 \text{ A dc}$ $V_{CE} = 5 \text{ V dc}$	$I_E = 0$ $V_{CB} = 10 \text{ V dc}$ $100 \text{ kHz} \leq f \leq 1 \text{ MHz}$	$I_C = 0.2 \text{ A dc}$ $V_{CE} = 10 \text{ V dc}$ $f = 10 \text{ MHz}$	$I_C = 5 \text{ A dc}$ $I_B = 0.5 \text{ A dc}$	$I_C = 5 \text{ A dc}$ $I_B = 0.5 \text{ A dc}$
Min	40	10	$\mu\text{F}$	1.5	$\text{V dc}$	$\text{V dc}$
Max	120		350	7.5	1.5	0.6

(1) Pulsed, (see 4.5.1).

## 2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3 and 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements documents cited in sections 3 and 4 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DODISS) and supplement thereto, cited in the solicitation (see 6.2).

## SPECIFICATION

## DEPARTMENT OF DEFENSE

MIL-PRF-19500 - Semiconductor Devices, General Specification for.

## STANDARD

## DEPARTMENT OF DEFENSE

MIL-STD-750 - Test Methods for Semiconductor Devices.

(Unless otherwise indicated, copies of the above specifications, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.3 Order of precedence. In the event of a conflict between the text of this document and the references cited herein (except for related associated specifications or specification sheets), the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

## 3. REQUIREMENTS

3.1 Qualification. Devices furnished under this specification shall be manufacturer's that are authorized by the qualifying activity for listing on the applicable qualified manufacturer's list before contract award (see 4.2 and 6.3).

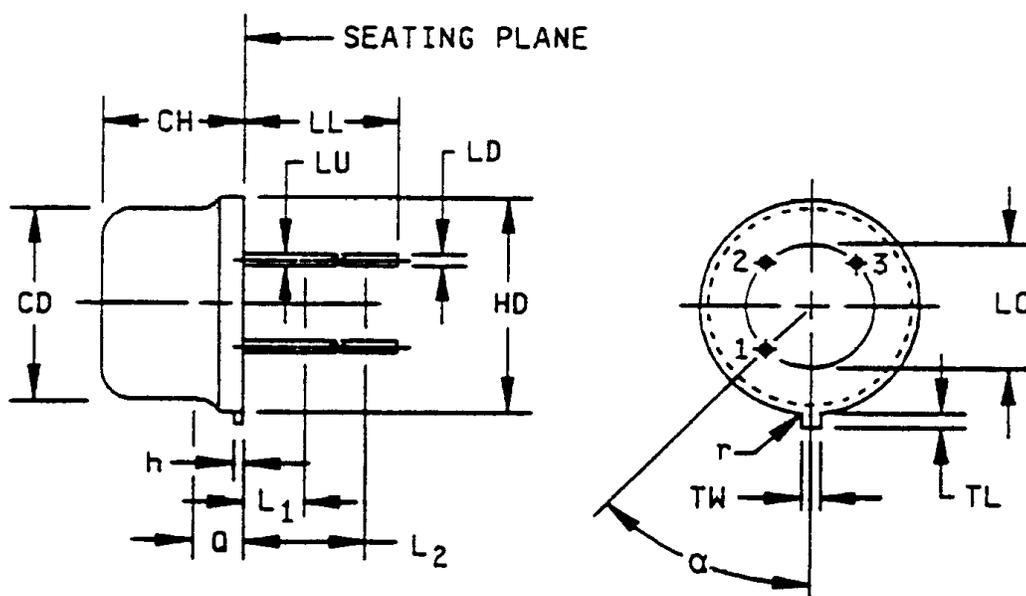


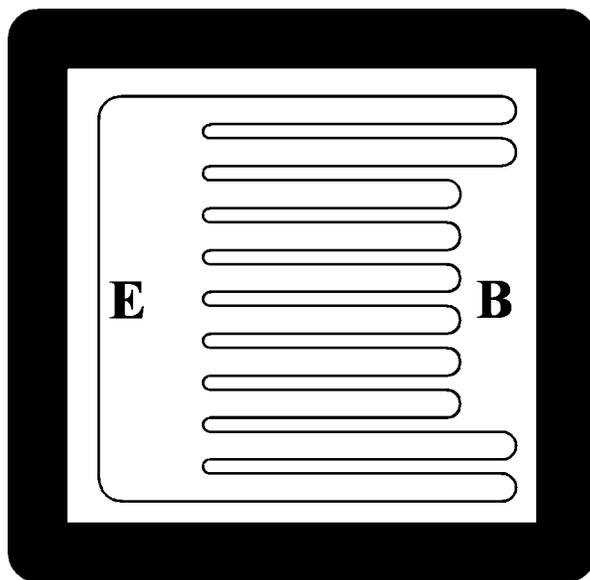
FIGURE 1. Physical dimensions .

Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	0.305	0.335	7.75	8.51	5
CH	0.240	0.260	6.10	6.60	
h	0.009	0.041	0.23	1.04	
HD	0.335	0.370	8.51	9.40	
LC	0.200 TP		5.08 TP		6
LD	0.016	0.021	0.41	0.53	7
LL	See notes 14 and 15				
LU	0.016	0.019	0.41	0.48	7
L <sub>1</sub>	---	0.050	---	1.27	7
L <sub>2</sub>	0.250	---	6.35	---	7
Q	---	0.050	---	1.27	13
r	---	0.010	---	0.25	11,12
TL	0.029	0.045	0.74	1.14	3
TW	0.028	0.034	0.71	0.86	10
$\alpha$	45° TP		45° TP		4, 6, 8, 9

## NOTES:

- Dimensions are in inches.
- Metric equivalents are given for general information only.
- Symbol TL is measured from HD maximum.
- Lead number 4 omitted on this variation.
- CD shall not vary more than 0.010. inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
- Leads at gauge plane 0.054 inch (1.37 mm) + 0.001 (0.03 mm) - 0.000 inch (0.00 mm) below seating plane shall be within 0.007 inch (0.18 mm) radius of true position (TP) relative to the tab. The device may be measured by direct methods.
- LD applies between L<sub>1</sub> and L<sub>2</sub>. Dimension LD applies between L<sub>2</sub> and LL minimum. Lead diameter shall not exceed 0.042 inch (1.07 mm) within L<sub>1</sub> and beyond LL minimum.
- Lead designation is as follows: 1 - emitter; 2 - base; 3 - collector.
- Lead number three is electrically connected to case.
- Beyond r maximum, TW shall be held for a minimum length of 0.011 inch (0.28 mm).
- r (radius) applies to both inside corners of tab.
- Tab shown omitted.
- Details of outline in this zone optional.
- For transistor types 2N4150S, 2N5237S, and 2N5238S, dimension LL = 0.500 inch (12.70 mm) minimum, and 0.750 inch (19.05 mm) maximum.
- For transistor types 2N4150, 2N5237, and 2N5238, dimension LL = 1.500 inch (38.10 mm) minimum, and 1.750 inches (44.45 mm) maximum

FIGURE 1. Physical dimensions - Continued.



NOTES:

- |                   |  |
|-------------------|--|
| 1. Chip size      | 120 x 120 mils $\pm$ 2 mils  |
| 2. Chip thickness | 10 $\pm$ 1.5mils nominal   |
| 3. Top metal      | Aluminum 30,000Å minimum, 33,000Å nominal  |
| 4. Back metal     | A. Al/Ti/Ni/Ag 12kÅ/3kÅ/7kÅ/7kÅ min. 15kÅ/5kÅ/10kÅ/10kÅ nom.<br>B. Gold 2,500Å minimum, 3,000Å nominal |
| 5. Backside       | Collector  |
| 6. Bonding pad    | B = 52 x 12 mils, E = 84 x 12 mils   |

FIGURE 2. JANHC and JANKC A-version die dimensions.

3.2 Associated specification. The individual item requirements shall be in accordance with MIL-PRF-19500 and as specified herein.

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500.

3.4 Interface requirements and physical dimensions. The interface requirements and physical dimensions shall be as specified in MIL-PRF-19500 and on figures 1 (TO- 5) and 2 (JANHC and JANKC) herein.

3.4.1 Lead material and finish. Lead finish shall be solderable as defined in MIL-PRF-19500, MIL-STD-750, and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see 6.2).

3.4.2 Construction. These devices shall be constructed in a manner and using materials which enable the devices to meet the applicable requirements of MIL-PRF-19500 and this document.

3.5 Marking. Marking shall be in accordance with MIL-PRF-19500.

3.6 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in 1.3, 1.4, and table I herein.

3.7 Electrical test requirements. The electrical test requirements shall be the subgroups specified in 4.4.2 and 4.4.3 herein.

3.8 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

#### 4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.4).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500.

4.3 Screening (JANS, JANTXV, and JANTX levels only). Screening shall be in accordance with MIL-PRF-19500 (table IV) and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see table IV of MIL-PRF-19500)	Measurement	
	JANS level	JANTX and JANTXV levels
3c	Thermal impedance (see 4.3.3)	Thermal impedance (see 4.3.3)
7	Hermetic seal (optional)	<u>1/</u>
9	ICBO2 and hFE1	Not applicable
10	48 hours minimum	48 hours minimum
11	ICBO2 ; hFE1; $\Delta$ ICBO2 = 100 percent of initial value or 50 nA dc, whichever is greater; $\Delta$ hFE1 = $\pm$ 15 percent of initial value.	ICBO2 and hFE1
12	See 4.3.1 240 hours minimum	See 4.3.1 80 hours minimum
13	Subgroups 2 and 3 of table I herein; $\Delta$ ICBO2 = 100 percent of initial value or 50 nA dc, whichever is greater; $\Delta$ hFE1 = $\pm$ 15 percent of initial value.	Subgroup 2 of table I herein; $\Delta$ ICBO2 = 100 percent of initial value or 50 nA dc, whichever is greater; $\Delta$ hFE1 = $\pm$ 15 percent of initial value.

1/ Hermetic seal test shall be performed in either screen 7 or screen 14.

4.3.1. Power burn-in conditions. Power burn-in conditions are as follows:

$V_{CB} = 10 - 30$  Vdc;  $T_A =$  Room ambient as defined in the general requirements of MIL-STD-750, paragraph 4.5. Power shall be applied to the device to achieve a Junction temperature,  $T_J = 135^\circ\text{C}$  minimum and minimum  $P_D = 75$  percent of maximum rated  $P_T \text{ max}$  as defined in 1.3.

4.3.3 Thermal impedance ( $Z_{\theta JX}$  measurements). The  $Z_{\theta JX}$  measurements shall be performed in accordance with MIL-STD-750, Method 3131.

- a.  $I_M$  measurement current ----- 10 mA.
- b.  $I_H$  forward heating current ----- 1 A.
- c.  $t_H$  heating time ----- 100 ms.
- d.  $t_{MD}$  measurement delay time ----- 30 – 60  $\mu$ s.
- e.  $V_{CE}$  collector-emitter voltage ----- 16 V dc minimum.

The maximum limit for  $Z_{\theta JX}$  under these test conditions are  $Z_{\theta JX}(\text{max}) = 12 \text{ }^\circ\text{C/W}$ .

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500 and as specified herein. If alternate screening is being performed per MIL-PRF-19500, a sample of screened devices shall be submitted to and pass the requirements of group A1 and A2 inspection only (table VIb, group B, subgroup 1 is not required to be performed again if group B has already been satisfied in accordance with 4.4.2).

4.4.1 Group A inspection. Group A inspection shall be conducted with MIL-PRF-19500, and Table I herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in VIa (JANS) of 4.4.2.1. Electrical measurements (end-points) and delta requirements shall be in accordance with group A, subgroup 2 and 4.5.3 herein. See 4.4.2.2 for JAN, JANTX, and JANTXV group B testing. Electrical measurements (end-points) and delta requirements JAN, JANTX, and JANTXV shall be after each step in 4.4.2.2 and shall be in accordance with group A, subgroup 2 and 4.5.3 herein.

4.4.2.1 Group B inspection, table VIa (JANS) of MIL-PRF-19500.

Subgroup	Method	Condition
B4	1037	$V_{CB} = 10 - 30 \text{ V dc}$ .
B5	1027	$V_{CB} = 10 - 30 \text{ V dc}$ ; $T_A = 125^\circ\text{C} \pm 25^\circ\text{C}$ for 96 hours with $P_T$ adjusted according to the chosen $T_A$ to give $T_J = 275^\circ\text{C}$ minimum. Optionally the test may be performed for a minimum of 216 hours with $P_T$ and $T_A$ adjusted to achieve a $T_J = 225^\circ\text{C}$ minimum. Power dissipation $P_D \geq 75$ percent of maximum rated $P_T$ shall be applied. $n = 45$ , $c = 0$ . (Note: If a failure occurs, resubmission shall be at the test conditions of the original sample.)
B6	3131	See 4.5.2.

4.4.2.2 Group B inspection, (JAN, JANTX, and JANTXV). Separate samples may be used for each step. In the event of a group B failure, the manufacturer may pull a new sample at double size from either the failed assembly lot or from another assembly lot from the same wafer lot. If the new "assembly lot option is exercised, the failed assembly lot shall be scrapped.

Step	Method	Condition
1	1039	Steady-state life: Test condition B, 340 hours, $V_{CB} = 10 - 30$ V dc. Power shall be applied to achieve a junction temperature $T_J = 150^\circ\text{C}$ minimum and power dissipation $P_D \geq 75$ percent of maximum rated $P_T$ as defined in 1.3. No heat sink or forced-air cooling on the devices shall be permitted, $n = 45$ devices, $c = 0$ .
2	1039	The steady state life test of step 1 shall be extended to 1,000 hours for each die design. Samples shall be selected from a wafer lot every twelve months of wafer production. Group B step 2 shall not be required more than once for any single wafer lot. $n = 45$ , $c = 0$ .
3	1032	High-temperature life (non-operating), $T_A = +200^\circ\text{C}$ . $n = 22$ , $c = 0$

4.4.2.3 Group B sample selection. Samples selected from group B inspection shall meet all of the following requirements:

- For JAN, JANTX, and JANTXV samples shall be selected randomly from a minimum of three wafers (or from each wafer in the lot) from each wafer lot. For JANS, samples shall be selected from each inspection lot. See MIL-PRF-19500.
- Must be chosen from an inspection lot that has been submitted to and passed group A, subgroup 2, conformance inspection. When the final lead finish is solder or any plating prone to oxidation at high temperature, the samples for life test (subgroups B4 and B5 for JANS, and group B for JAN, JANTX, and JANTXV) may be pulled prior to the application of final lead finish.

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VII of MIL-PRF-19500, and in 4.4.3.1 (JANS).and 4.4.3.2 (JAN, JANTX, and JANTXV) herein for group C testing. Electrical measurements (end points) and delta requirements shall be in accordance with group A, subgroup 2 and 4.5.3 herein.

4.4.3.1 Group C inspection, table VII (JANS) of MIL-PRF-19500.

Subgroup	Method	Condition
C2	2036	Test condition E.
C6	1026	$V_{CB} = 10 - 30$ V dc. Power shall be applied to achieve a junction temperature $T_J = 150^\circ\text{C}$ minimum and power dissipation $P_D \geq 75$ percent of maximum rated $P_T$ as defined in 1.3. No heat sink or forced-air cooling on the devices shall be permitted, $n = 45$ devices, $c = 0$ .

4.4.3.2 Group C inspection, table VII (JAN, JANTX, and JANTXV) of MIL-PRF-19500.

Subgroup	Method	Condition
C2	2036	Test condition E.
C6		Not applicable

4.4.3.3 Group C sample selection. Samples for subgroups in group C shall be chosen at random from any lot containing the intended package type and lead finish procured to the same specification which is submitted to and passes group A tests for conformance inspection. Testing of a subgroup using a single device type enclosed in the intended package type shall be considered as complying with the requirements for that subgroup.

4.4.4 Group E inspection. Group E inspection shall be performed for qualification or requalification only. The tests specified in Table II herein must be performed to maintain qualification.

4.5 Method of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

4.5.2 Thermal resistance. Thermal resistance measurements shall be conducted in accordance with method 3131 of MIL-STD-750. The following conditions shall apply:

- a.  $I_M$ : Collector current ..... 10 mA.
- b.  $V_{CE}$ : Measurement current (same as  $V_H$ )..... 10 V dc.
- c.  $I_H$ : Collector heating current..... 0.375 A.
- d.  $V_H$ : Collector-emitter heating voltage ..... 10 V dc.
- e.  $t_H$ : Heating time ..... 1.0 s.
- f.  $t_{MD}$ : Measurement delay time ..... 30 to 60  $\mu$ s.
- g.  $t_{SW}$ : Sampling window time..... 10  $\mu$ s maximum.

4.5.3 Delta requirements. Delta requirements shall be as specified below:

Step	Inspection	MIL-STD-750		Symbol	Limit	Unit
		Method	Conditions			
1	Collector-base cutoff current	3036	Bias condition D, $V_{CB} = 80$ V dc	$\Delta I_{CB02}$ (1)	100 percent of initial value or 50 nA dc, whichever is greater.	
2	Forward current transfer ratio	3076	$V_{CE} = 5$ V dc; $I_C = 5$ A dc; pulsed see 4.5.2	$\Delta h_{FE2}$ (1)	$\pm 20$ percent change from initial reading.	

(1) Devices which exceed the group A limits for this test shall not be accepted.

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TABLE I. Group A inspection.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1</u> <u>2/</u>						
Visual and mechanical examination <u>3/</u>	2071	n = 45 devices, c = 0				
Solderability <u>3/</u> <u>5/</u>	2026	n = 15 leads, c = 0				
Resistance to <u>3/</u> <u>4/</u> <u>5/</u> Solvent	1022	n = 15 devices, c = 0				
Temperature cycling <u>3/</u> <u>5/</u>	1051	Test condition C, 25 cycles. n = 22 devices, c = 0				
Hermetic seal <u>5/</u>	1071	n = 22 devices, c = 0				
Fine leak Gross leak						
Electrical Measurements <u>5/</u>		Group A, subgroup 2				
Bond strength <u>3/</u> <u>5/</u>	2037	Precondition T <sub>A</sub> = +250°C at t = 24 hrs or T <sub>A</sub> = +300°C at t = 2 hrs, n = 11 wires, c = 0				
<u>Subgroup 2</u>						
Collector to base Cutoff current	3036		I <sub>CBO1</sub>		10	μA dc
2N4150, 2N4150S 2N5237, 2N5237S 2N5238, 2N5238S		V <sub>CB</sub> = 100 V dc V <sub>CB</sub> = 150 V dc V <sub>CB</sub> = 200 V dc				
Breakdown voltage, Collector to emitter	3011	Bias condition D, I <sub>C</sub> = 0.1 A dc, pulsed (see 4.5.1)	V <sub>(BR)CEO</sub>			V dc
2N4150, 2N4150S 2N5237, 2N5237S 2N5238, 2N5238S				70 120 170		

See footnotes at end of table.

TABLE I. Group A inspection - Continued.

Inspection 1/	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 2</u> – continued						
Emitter to base cutoff Current	3061	$V_{BE} = 7 \text{ V dc}$	$I_{EBO1}$		10	A dc
Collector to emitter cutoff current	3041	Bias condition D	$I_{CEO1}$		10	$\mu\text{A dc}$
2N4150, 2N4150S 2N5237, 2N5237S 2N5238, 2N5238S		$V_{CE} = 60 \text{ V dc}$ $V_{CE} = 110 \text{ V dc}$ $V_{CE} = 160 \text{ V dc}$				
Collector to emitter cutoff current	3041	Bias condition A $V_{BE} = 0.5 \text{ V dc}$	$I_{CEX}$		10	$\mu\text{A dc}$
2N4150, 2N4150S 2N5237, 2N5237S 2N5238, 2N5238S		$V_{CE} = 60 \text{ V dc}$ $V_{CE} = 110 \text{ V dc}$ $V_{CE} = 160 \text{ V dc}$				
Emitter to base cutoff current	3061	Bias condition D, $V_{BE} = 5 \text{ V dc}$	$I_{EBO2}$		0.1	$\mu\text{A dc}$
Collector to base cutoff current	3036	Bias condition D, $V_{CB} = 80 \text{ V dc}$	$I_{CBO}$		0.1	$\mu\text{A dc}$
Forward-current transfer ratio	3076	$V_{CE} = 5 \text{ V dc}$ , $I_C = 1 \text{ A dc}$ , pulsed (see 4.5.1)	$h_{FE1}$			
2N4150, 2N4150S 2N5237, 2N5237S 2N5238, 2N5238S				50 50 50	200 225 225	
Forward-current transfer ratio	3076	$V_{CE} = 5 \text{ V dc}$ , $I_C = 5 \text{ A dc}$ , pulsed (see 4.5.1)	$h_{FE2}$	40	120	
Collector to emitter voltage (saturated)	3071	$I_C = 5 \text{ A dc}$ , $I_B = 0.5 \text{ A dc}$ pulsed (see 4.5.1)	$V_{CE(sat)1}$		0.6	V dc
Collector to emitter voltage (saturated)	3071	$I_C = 10 \text{ A dc}$ , $I_B = 1 \text{ A dc}$ pulsed (see 4.5.1)	$V_{CE(sat)2}$		2.5	V dc

See footnotes at end of table.

TABLE I. Group A inspection - Continued.

Inspection 1/	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 2</u> – continued						
Base emitter voltage saturation	3066	Test condition A, $I_C = 5$ A dc, $I_B = 0.5$ A dc pulsed (see 4.5.1)	$V_{BE(sat)1}$		1.5	V dc
Base emitter voltage saturation	3066	Test condition A, $I_C = 10$ A dc, $I_B = 1$ A dc pulsed (see 4.5.1)	$V_{BE(sat)2}$		2.5	V dc
Forward-current transfer ratio	3076	$V_{CE} = 5$ V dc, $I_C = 10$ A dc pulsed (see 4.5.1)	$h_{FE3}$	10		
<u>Subgroup 3</u>						
High temperature operation:		$T_A = +150^\circ\text{C}$				
Collector to emitter cutoff current	3041	Bias condition A, $V_{BE} = -0.5$ V dc	$I_{CEX2}$		100	$\mu\text{A dc}$
		$V_{CE} = 60$ V dc $V_{CE} = 110$ V dc $V_{CE} = 160$ V dc				
Low temperature operation:		$T_A = -55^\circ\text{C}$				
Forward-current transfer ratio	3076	$V_{CE} = 5$ V dc, $I_C = 5$ A dc, Pulsed (see 4.5.1)	$h_{FE4}$	20		
<u>Subgroup 4</u>						
Magnitude of common-emitter small-signal short-circuit forward-current transfer ratio	3306	$V_{CE} = 10$ V dc, $I_C = 0.2$ A dc, $f = 10$ MHz	$ h_{fe} $	1.5	7.5	
Small-signal short-circuit forward-current transfer ratio	3206	$V_{CE} = 5$ V dc, $I_C = 50$ mA dc, $f = 1$ kHz	$h_{fe}$			
				40	160	
				40	160	
				40	250	

See footnotes at end of table.

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 4</u> continued						
Open circuit output capacitance	3236	$V_{CB} = 10 \text{ V dc}, I_E = 0, 100 \text{ kHz} \leq f \leq 1 \text{ MHz}$	$C_{obo}$		350	pF
Pulse response	3251	Test condition A				
Delay time		See figure 4	$t_d$		50	ns
Rise time		See figure 4	$t_r$		500	ns
Storage time		See figure 4	$t_s$		1.5	$\mu\text{s}$
Fall time		See figure 4	$t_f$		500	ns
<u>Subgroup 5</u>						
Safe operating area (continuous dc)	3051	$T_C = +25^\circ\text{C}, t = 1.0 \text{ s},$				
<u>Test 1</u>		$V_{CE} = 40 \text{ V dc}, I_C = 0.22 \text{ A dc}$				
<u>Test 2</u>		$V_{CE} = 70 \text{ V dc}, I_C = 90 \text{ mA dc}$				
<u>Test 3</u>						
2N5237, 2N5237S only		$V_{CE} = 120 \text{ V dc}, I_C = 15 \text{ mA dc}$				
2N5238, 2N5238S only		$V_{CE} = 170 \text{ V dc}, I_C = 3.5 \text{ mA dc}$				
Clamped inductive sweep	3053	$T_C = +100^\circ\text{C}$ minimum, $I_B = 0.5 \text{ A dc}, I_C = 5 \text{ A dc},$ (see figure 5)				
Electrical measurements		See paragraph 4.5.3				
<u>Subgroup 7 5/</u>						
Decap internal visual (design verification)	2075	$n = 1 \text{ device}, c = 0$				

1/ For sampling plan, see MIL-PRF-19500.

2/ For resubmission of failed subgroup A1, double the sample size of the failed test or sequence of tests.

3/ Separate samples may be used.

4/ Not required for JANS.

5/ Not required for laser marked devices.

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TABLE II. Group E inspection (all quality levels) - For qualification and requalification only

Inspection	MIL-STD-750		Qualification
	Method	Conditions	
<u>Subgroup 1</u>			12 devices c = 0
Temperature cycling (air to air)	1051	Test condition C, 500 cycles	
Hermetic seal	1071		
Fine leak Gross leak			
Electrical measurements		See group A, subgroup 2 and 4.5.3 herein.	
<u>Subgroup 2</u>			45 devices c = 0
Intermittent life	1037	Intermittent operation life: $V_{CB} = 10 \text{ V dc}$ , 6,000 cycles, $\Delta T_J \geq +100^\circ\text{C}$ ; forced air cooling allowed on cooling cycle only.	
Electrical measurements		See group A, subgroup 2 and 4.5.3 herein.	
<u>Subgroup 3, 4, and 5</u>			
Not applicable			

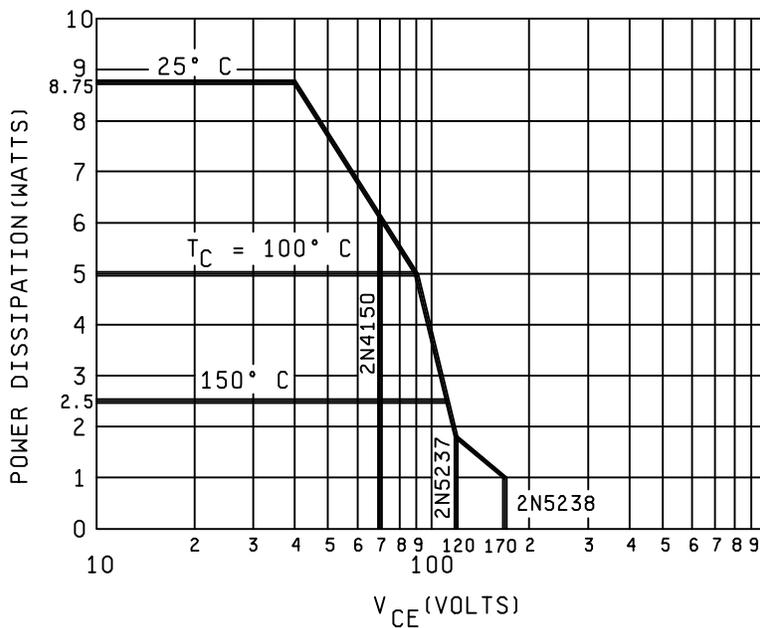


FIGURE 3. Maximum operating conditions - dc forward biased mode.

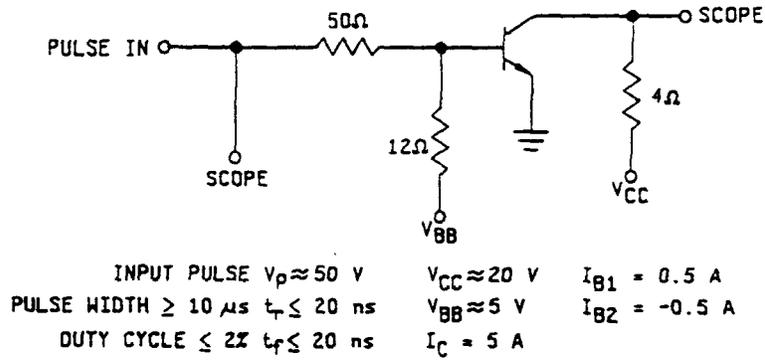
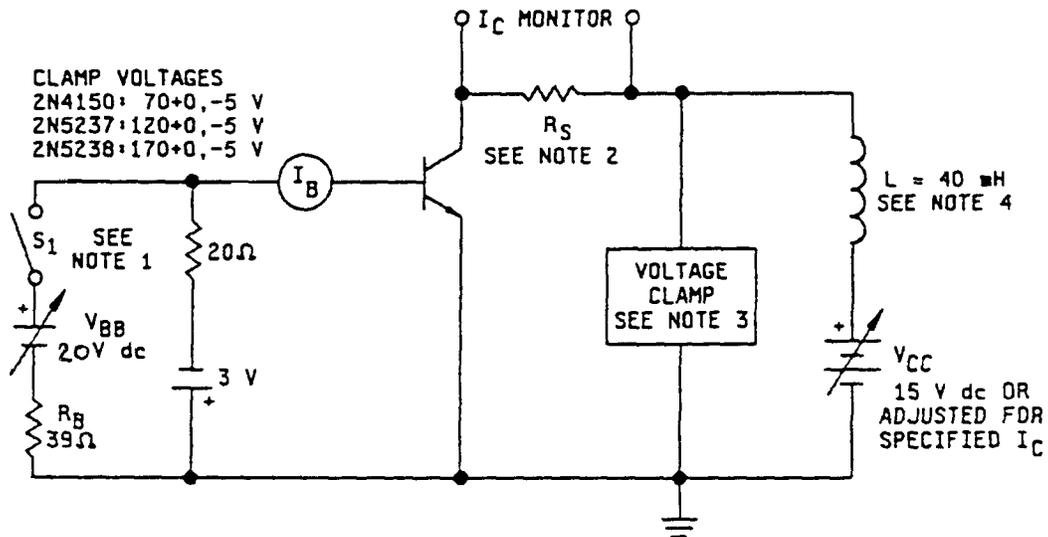


FIGURE 4. Speed of response test circuit.



NOTES:

1. An appropriate pulse generator may be substituted.
2.  $R_S \leq 1.0 \Omega$  noninductive.
3. Clamp voltage: 2N4150: 70 V dc +0 V dc, -5 V dc; 2N5237: 120 V dc +0 V dc, -5 V dc; 2N5238: 170 V dc +0 V dc, -5 V dc
4. STANCOR C-2691 or equivalent; 2 in series.

FIGURE 5. Clamped inductive sweep test circuit.

5. PACKAGING

5.1 Packaging. Packaging shall prevent mechanical damage of the devices during shipping and handling and shall not be detrimental to the device. When actual packaging of material is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Points' packaging activity within the Military Department or Defense Agency, or within the Military Departments' System Command. Packaging data retrieval is available from the managing Military Departments' or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

5.2 Marking. Unless otherwise specified (see 6.2), marking shall be in accordance with MIL-PRF-19500.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory.)

6.1 Notes. The notes specified in MIL-PRF-19500 are applicable to this specification.

6.2 Acquisition requirements. Acquisition documents must specify the following:

- a. Title, number, and date of this specification.
- b. Issue of DoDISS to be cited in the solicitation, and if required, the specific issue of individual documents referenced (see 2.2).
- c. Packaging requirements (see 5.1).
- d. Type designation and quality assurance level.

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturer's List QML No.19500 whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or purchase orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from Defense Supply Center Columbus, ATTN: DSCC-VQE, 3990 East Broad Street, Columbus, OH 43216-5000.

6.4 Suppliers of JANHC and JANKC die. The qualified die suppliers with the applicable letter version (example, JANHCA2N4150) will be identified on the QML.

JANC ordering information			
PIN	Manufacturers		
	43611		
2N4150	JANHCA2N4150 JANKCA2N4150		

6.5 Changes from previous issue. Marginal notations are not used in this revision to identify changes with respect to the previous issue due to the extensiveness of the changes.

Custodians:

Army - CR  
Navy - EC  
Air Force - 11  
DLA - CC

Preparing activity:

DLA - CC

(Project 5961 - 2320)

Review activities:

Army - MI, SM  
Air Force - 13, 19, 99

## STANDARDIZATION DOCUMENT IMPROVEMENT PROPOSAL

### INSTRUCTIONS

1. The preparing activity must complete blocks 1, 2, 3, and 8. In block 1, both the document number and revision letter should be given.
2. The submitter of this form must complete blocks 4, 5, 6, and 7.
3. The preparing activity must provide a reply within 30 days from receipt of the form.

NOTE: This form may not be used to request copies of documents, nor to request waivers, or clarification of requirements on current contracts. Comments submitted on this form do not constitute or imply authorization to waive any portion of the referenced document(s) or to amend contractual requirements.

<b>I RECOMMEND A CHANGE:</b>	1. DOCUMENT NUMBER MIL-PRF-19500/394E	2. DOCUMENT DATE 000714
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<b>3. DOCUMENT TITLE</b> SEMICONDUCTOR DEVICE, TRANSISTOR, NPN, SILICON, POWER SWITCHING TYPES: 2N4150, 2N5237, 2N5238, 2N4150S, 2N5237S, AND 2N5238S JAN, JANTX, JANTXV, JANS, JANHC AND JANKC
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4. NATURE OF CHANGE (Identify paragraph number and include proposed rewrite, if possible. Attach extra sheets as needed.)
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5. REASON FOR RECOMMENDATION
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6. SUBMITTER
--------------

a. NAME (Last, First, Middle initial)	b. ORGANIZATION	
c. ADDRESS (Include Zip Code)	d. TELEPHONE (Include Area Code) COMMERCIAL DSN FAX EMAIL	7. DATE SUBMITTED

8. PREPARING ACTIVITY
-----------------------

a. Point of Contact Alan Barone	b. TELEPHONE		
	Commercial	DSN	FAX
	614-692-0510	850-0510	614-692-6939
			EMAIL alan_barone@dsccl.dla.mil

c. ADDRESS Defense Supply Center Columbus, ATTN: DSCC-VAC, 3990 East Broad Street, Columbus, OH 43213-1199	IF YOU DO NOT RECEIVE A REPLY WITHIN 45 DAYS, CONTACT: Defense Standardization Program Office (DLSC-LM) 8725 John J. Kingman, Suite 2533, Fort Belvoir, VA 22060-6221 Telephone (703) 767-6888 DSN 427-6888
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